

CLAIM AMENDMENTS

1. (Currently Amended) A semiconductor device comprising:
a porous low-k dielectric film ~~formed~~ on a substance;
an opening portion for wiring ~~formed~~ in the porous low-k dielectric film;
dielectric films ~~cover~~ covering only side surfaces of the opening portion, each of the dielectric films having a dielectric constant ~~of not exceeding 3 or less~~; and
a wiring ~~formed~~ in the opening portion ~~through~~ on the dielectric ~~film~~ films.
2. (Original) The semiconductor device according to claim 1, wherein the dielectric films include a fluorinated polyarylene film or an amorphous carbon fluoride.
3. (Currently Amended) The semiconductor device according to claim 1, wherein the porous low-k dielectric film ~~includes any one~~ is selected from the group consisting of a porous MSQ, a porous HSQ, a hybrid film containing both methyl and hydroxyl groups, and a porous organic film containing carbon as a major component.
4. (Currently Amended) A method for manufacturing a semiconductor device comprising ~~the steps of~~:
forming a porous low-k dielectric film on a substrate;
forming an opening portion for wiring in the porous low-k dielectric film;
forming a dielectric film having a dielectric constant ~~of no more than 3 or less~~ on an entire surface of the substrate, including side surfaces of the opening portion;
removing unnecessary dielectric film ~~formed on the area~~ areas other than the side surfaces of the opening portion; and
forming, after ~~the step of~~ removing unnecessary dielectric film, a conductive film in the opening portion ~~through~~ on the dielectric ~~film~~ films.
5. (Currently Amended) The method for manufacturing a semiconductor device according to claim 4, wherein the dielectric ~~film includes~~ films include one of a fluorinated polyarylene film ~~or~~ and an amorphous carbon fluoride.
6. (Currently Amended) The method for manufacturing a semiconductor device according to claim 4, wherein the porous low-k dielectric film ~~includes any one~~ is selected from the group consisting of a porous MSQ, a porous HSQ, a hybrid film containing both

In re Appln. of Naruhiko KAJI
Application No. Unassigned

methyl and hydroxyl groups, and a porous organic film containing carbon as a major component.